Time		Coherence	Qubit	Material	Host	Date	Reference	Source
57	s	T_1	LD/e	GaAs/AlGaAs	2D	2018-08	1	p3 and Fig. 4a
43	s	T_1	LD/i	Si:P	imp	2024-03	2	Tab. 2 and Fig. 4
30	s	T_1	LD/i	Si:P	imp	2017-03	3	Fig. 2b the lowest point
16	s	T_1	LD/i	Si:P	imp	2023-11	4	Tab. I
11	s[a]	T_1	LD/i	Si:P	imp	2023-02	5	p6
10	s	T_1	LD/e	GaAs/AlGaAs	2D	2017-10	6	Fig. 2 the lowest green point
9.8	s	T_1	LD/i	Si:P	imp	2019-05	7	Fig. 2c
9.3	s	T_1	LD/i	Si:P	imp	2018-03	8	p3 and Fig. 1f
9	s	T_1	LD/e	Si/SiO_2	1D	2021-03	9	p3 and Fig. 3a the leftmost blue point
6.5	s	T_1	LD/i	^{28}Si:P	imp	2023-02	10	Fig. 3c
6	s	T_1	LD/i	Si:P	imp	2010-09	11	p2
5	s[b]	T_1	LD/e	Si/SiGe	2D	2019-04	12	p4
4.2	s	T_1	LD/i	Si:P	imp	2019-01	13	p3
3.4	s	T_1	LD/i	^{28}Si:P	imp	2021-01	14	p6 and SFig. 3c
3	s	T_1	LD/i	^{28}Si:P	imp	2016-10	15	p3
3	s	T_1	ST/e	Si/SiGe	2D	2012-01	16	p4
2.8	s	T_1	LD/e	Si/SiGe	2D	2011-04	17	p3 and Fig. 3
2.6	s	T_1	LD/e	Si/SiO_2	2D	2013-06	18	p3
1.8	s	T_1	LD/i	Si:P	imp	2013-06	19	Fig. 3
1.6	s	T_1	LD/e	$^{28}Si/SiO_2$	2D	2022-03	20	p4 and Fig. 3c
1.3	s	T_1	LD/i[c]	^{28}Si:P	imp	2016-10	21	p4
1.3	s	T_1	LD/i	Si:P	imp	2018-11	22	p3 and Fig. 2b
1	s	T_1	LD/e	^{28}Si/SiGe	2D	2020-03	23	p6 and Fig. 4a
1	s	T_1	LD/e	$^{28}Si/SiO_2$	2D	2018-10	24	p2
1	s	T_1	LD/e	GaAs/AlGaAs	2D	2008-01	25	p4 and Fig. 3c the leftmost blue point
0.7	s	T_1	LD/i	Si:P	imp	2012-09	26	p3
0.6	s[d]	T_1	LD/e	Si/SiGe	2D	2009-08	27	Fig. 5
0.5	s[e]	T_1	ST/e	$^{28}Si/SiO_2$	2D	2020-04	28	Fig. 4 the leftmost black point
0.35	s[f]	T_1	HY/e	BLG	2D	2024-01	29	Fig. 3b
0.17	s	T_1	LD/e	Si/SiGe	2D	2016-11	30	Fig. 6
0.16	s[g]	T_1	LD/e	Si/SiGe	2D	2019-04	12	Fig. 2
0.15	s[h]	T_1	LD/e	$^{28}Si/SiO_2$	2D	2018-08	31	p2 and p4
0.14	s	T_1	ST/e	Si/SiGe	2D	2012-04	32	Fig. 2d
0.13	s	T_1	LD/e	^{28}Si/SiGe	2D	2019-11	33	p4
90	ms	T_1	LD/e	Si/SiO_2	2D	2020-06	34	Fig. 1c
85	ms	T_1	LD/e	GaAs/AlGaAs	2D	2014-12	35	p2 and Fig. 3
50	ms	T_1	LD/e	Si/SiGe	2D	2018-02	36	p1 and ED Fig. 3b
40	ms	T_1	LD/e	Si/SiO_2	2D	2010-03	37	p4 and Fig. 4 the leftmost red point
34	ms	T_1	ST/e	BLG	2D	2024-01	29	Fig. 3b
32	ms	T_1	LD/h	Ge/SiGe	2D	2020-08	38	p3
32	ms	T_1	LD/e	^{28}Si/SiGe	2D	2022-12	39	p3
22	ms[i]	T_1	LD/e	Si/SiGe	2D	2022-08	40	p2 and ED Fig. 4b-d
20	ms	T_1	HY/e[j]	^{28}Si/SiGe	2D	2022-03	41	p5
16	ms	T_1	LD/h	Ge/SiGe	2D	2021-03	42	Fig. S5 dot 3
15	ms[k]	T_1	ST/e	$^{28}Si/SiO_2$	2D	2020-04	28	Fig. 4 the rightmost black point
11	ms[l]	T_1	LD/e	$^{28}Si/SiO_2$	2D	2024-03	43	p3
10	ms	T_1	LD/e	Si/SiO_2	1D	2022-03	44	p2 and Fig. 2a
8.4	ms	T_1	LD/h	BLG	2D	2022-05	45	p5 and Fig. 4
5	ms	T_1	LD/i	^{28}Si:B	imp	2020-07	46	p3 and Fig. 3b
5	ms[m]	T_1	ST/e	$^{28}Si/SiO_2$	2D	2021-01	47	p4 and Fig. 1d

TABLE I-1. Spin coherence times (part 1). Superscripts stand for the following. [a]: Dot D3. [b]: No micromagnet. [c]: Qubit defined in the rotating frame. [d]: *(estimated)* Fig. 5 the lowest point. [e]: At 0.04 K. [f]: Valley degree of freedom. [g]: With micromagnet. [h]: At 0.1 K. [i]: The average over the three qubits. [j]: EO qubit. [k]: At 1.5 K. [l]: At 1 K. [m]: Lifetime of T_- state.

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